

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): A semiconductor device comprising:

a first dielectric film formed in a first region on a single crystalline substrate ~~[[and]]~~;

a second dielectric film formed in a second region on said single crystalline substrate adjacent to said first region; and

a predetermined film made of ~~one of~~ a polycrystalline material ~~and an amorphous material~~, and formed at ~~[[the]]~~ a border between said first and second dielectric films, at least a surface of said predetermined film being oxidized.

Claim 2 (original): The semiconductor device according to claim 1, wherein said first dielectric film is thicker than said second dielectric film, and said predetermined film is formed on a side surface of said first dielectric film.

Claim 3 (original): The semiconductor device according to claim 1, wherein said predetermined film has a portion interposed between said first and second dielectric films at said border.

Claims 4-9 (canceled)

Claim 10 (new): A semiconductor device comprising:

a first dielectric film formed in a first region on a single crystalline substrate and in direct contact with said single crystalline substrate;

a second dielectric film formed in a second region on said single crystalline substrate adjacent to said first region and in direct contact with said single crystalline substrate; and

a predetermined film made of an amorphous material and formed at a border between said first and second dielectric films, at least a surface of said predetermined film being oxidized,

wherein said first dielectric film is thicker than said second dielectric film, and

said predetermined film is formed on a side surface of said first dielectric film and is not formed on a top surface of said first dielectric film.

Claim 11 (new): The semiconductor device of claim 10, wherein said predetermined film has a portion interposed between said first and second dielectric films at said border and in direct contact with said single crystalline substrate.

Claim 12 (new): The semiconductor device according to claim 10, wherein said predetermined film is entirely oxidized.

Claim 13 (new): A semiconductor device comprising:

a first dielectric film formed in a first region on a single crystalline substrate and in direct contact with said single crystalline substrate;

a second dielectric film formed in a second region on said single crystalline substrate adjacent to said first region and in direct contact with said single crystalline substrate; and

a predetermined film which is made of an amorphous material, formed at a border between said first and second dielectric films, at least a surface of said predetermined film being oxidized,

wherein said predetermined film has a portion interposed between said first and second dielectric films at said border and in direct contact with said single crystalline substrate.

Claim 14 (new): The semiconductor device according to claim 13, wherein said predetermined film is entirely oxidized.